

OPA6611

N Side-Up

Red LED Chip

GaAlAs/GaAs

1. Material Substrate GaAs (P Type)
Epitaxial Layer GaAlAs (N/P Type)

2. Electrode N(Cathode) Side Gold Alloy
P(Anode) Side Gold Alloy

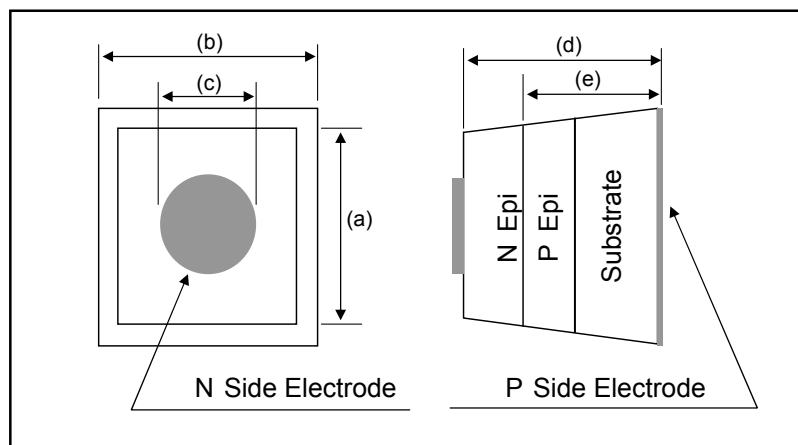
3. Electro-Optical Characteristics

Parameter	Symbol	Min	Typ	Max	Unit	Condition
Forward Voltage	$V_{F(1)}$		1.6		V	IF=1mA
	$V_{F(2)}$		1.9	2.2	V	IF=20mA
Reverse Voltage	V_R	6			V	IR=10uA
Brightness	Iv	500	900		mcd	IF=20mA
Wavelength	λ_d		640		nm	IF=20mA
	$\Delta\lambda$		20		nm	IF=20mA

※ Note : Brightness is measured by Sorter E/T system with bare chip.

4. Mechanical Data

(a) Emission Area	-----	10mil x 10mil
(b) Bottom Area	-----	12mil x 12mil
(c) Bonding Pad	-----	130um
(d) Chip Thickness	-----	11mil
(e) Junction Height	-----	8.8mil



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